

IN THE SPECIFICATION

Please add the following paragraph after the TITLE and before the “BACKGROUND OF THE INVENTION” section starting on page 1, of the specification.

This is a U.S. national stage of application No. PCT/JP2004/003638, filed on 18 March 2004. Priority under 35 U.S.C. §119(a) and 35 U.S.C. §365(b) is claimed from Japanese Application No. 2003-79279, filed 24 March 2003, the disclosure of which is also incorporated herein by reference.

Please replace the paragraph on page 15, beginning on line 18, with the following:

Fig. 9 is a view schematically showing a configuration of an MIM capacitor 21. In this figure, reference numeral 22 denotes a Si monocrystal substrate (hereinafter simply referred to as a Si substrate), and the resistivity thereof is from 0.01 to $15 \Omega \cdot \text{cm}$, for example. Reference numeral 23 denotes an element isolation oxide film for isolating elements, which is formed by thermal oxidation of the ~~Si substrate 22~~ Si substrate 22. Reference numeral 24 denotes a gate insulating film to be formed on the surface 22a of the Si substrate 22. The gate insulating film 24 is formed in the same manner as the formation of the gate insulating film 4 shown in the above-mentioned Fig. 1.

Please replace the paragraph starting on page 15, beginning on line 28 continuing onto page 16, ending on line 14, with the following:

Reference ~~numeral 45~~ numeral 25 denotes a gate electrode to be formed on the upper surface of the ~~gate-insulating film 4~~ gate insulating film 24. For example, the gate electrode is made of a noble metal such as Pt (platinum) or a high melting point metal such as TiN or TaN, the noble metal and the high melting point metal not reacting with a polycrystal Si film, a polycrystal SiGe film or the ~~gate-insulating film 4~~ gate insulating film 24. Reference ~~numeral 46~~ numeral 26 denotes a channel region. P (phosphorous) or the like is injected into an n channel and B (boron) or the like is injected into a p channel, and those channels are heat treated at temperatures of 800 to $1,000^\circ\text{C}$ for 10 to 30

minutes to be activated. Reference numeral 27 denotes a first interlayer insulating film, which for example comprises SiO₂ or the like and formed by CVD method or the like. Reference numeral 28 denotes an extraction electrode of the ~~channel 46~~channel 26. The extraction electrode 28 is formed in such a manner that a contact hole is formed in the first interlayer insulating film 27 by means of RIE (reactive ion etching) or the like, and a high melting point metal, such as Cu, Al, AlSi, Pt₂Si, TiN or TaN, is then provided in the contact hole.